

1.1 Scope.

This specification covers the device requirements for a high speed, low drift FET input operational amplifier.

1.2 Part Number.

The complete part number per Table 1 of this specification is as follows:

Device	Part Number
- 1	AD380SH/883B
- 2	AD381SH/883B
- 3	AD382SH/883B

1.2.3 Case Outline.

See Appendix 1 of General Specification ADI-H-1000: package outline:

Device	Package
- 1	H-12A
- 2	H-08B
- 3	H-12A

1.3 Absolute Maximum Ratings. ($T_A = +25^\circ\text{C}$ unless otherwise noted)

Positive Supply Voltage	+18V
Negative Supply Voltage	-18V
Input Signal	$\pm V_S$
Differential Input Signal	$\pm 2 \times V_S$
Output Short Circuit Current to Ground (Device - 1, 3)	80mA Continuous
Output Short Circuit Current to Ground (Device - 2)	20mA Continuous
Junction Temperature	+175°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering 10sec)	+300°C

1.5 Thermal Characteristics.

Thermal Resistance θ_{JC}	= 70°C/W for H-12A
θ_{JA}	= 100°C/W for H-12A
θ_{JC}	= 40°C/W for H-08B
θ_{JA}	= 150°C/W for H-08B

AD380/AD381/AD382 – SPECIFICATIONS

Test	Symbol	Device	Design Limit @ +25°C	Sub Group 1	Sub Group 2, 3	Sub Group 4	Test Condition ¹	Units
Open Loop Gain	A _{OL}	– 1	40,000			40,000	No Load	V/V min
		– 1	25,000			25,000	Note 2	V/V min
		– 2	100,000			100,000	Note 3	V/V min
		– 3	35,000			35,000	Note 2	V/V min
		– 3	150,000			150,000	Note 4	V/V min
Gain Bandwidth Product	GBP	– 1	200			200	f = 60kHz, C _C = 1pF	MHz min
			20			20	f = 60kHz, C _C = 10pF	
Slew Rate	SR	– 1	200			200	C _C = 1pF, 20V Swing	V/μs
		– 2, 3	20			20		
Output Voltage Swing	OVS	– 1	12			10	R _L = 200Ω	± V min
		– 2					R _L = 1kΩ	
		– 3					R _L = 200Ω	
Input Offset Voltage	V _{OS}	– 1	2.0	2.0				mV max
		– 2, 3	1.0	1.0				
Input Offset Voltage vs. Temperature	V _{OSTC}	– 1	50		50			± μV/°C max
		– 2, 3	10		10			
Output Short Circuit Current	I _{SC}	– 1	90			90	Short Circuit Current to Ground, Continuous	mA min
			220			220		mA max
		– 2	20			20		mA min
			220			220		mA max
		– 3	80			80		mA min
			220			220		mA max
Input Bias Current	I _{BIAS}	– 1	100			100	Either Input	pA max
		– 2	100			100		
		– 3	100			100		
Input Offset Current	I _{OS}	– 1, 2, 3	5					pA typ
Common-Mode Range	V _{DIF}	– 1, 2, 3	10					± V max
Common-Mode Rejection Ratio	CMRR	– 1	60			60	V _{INPUT} = ± 10V	dB min
		– 2, 3	80			80		
Operating Power Supply	V _{SS}	– 1	6					± V min
			20					± V max
		– 2, 3	5					± V min
			18					± V max
Quiescent Current	I _{SS}	– 1	17			17		± mA max
		– 2, 3	6			6		

NOTES

¹T_A = +25°C, V_S = ±15V, unless otherwise specified.

²V_{OUT} = +10V to 0V 200Ω load, V_{OUT} = 0V to –10V 200Ω load.

³V_{OUT} = +10V to 0V 2k load, V_{OUT} = 0V to –10V 2k load.

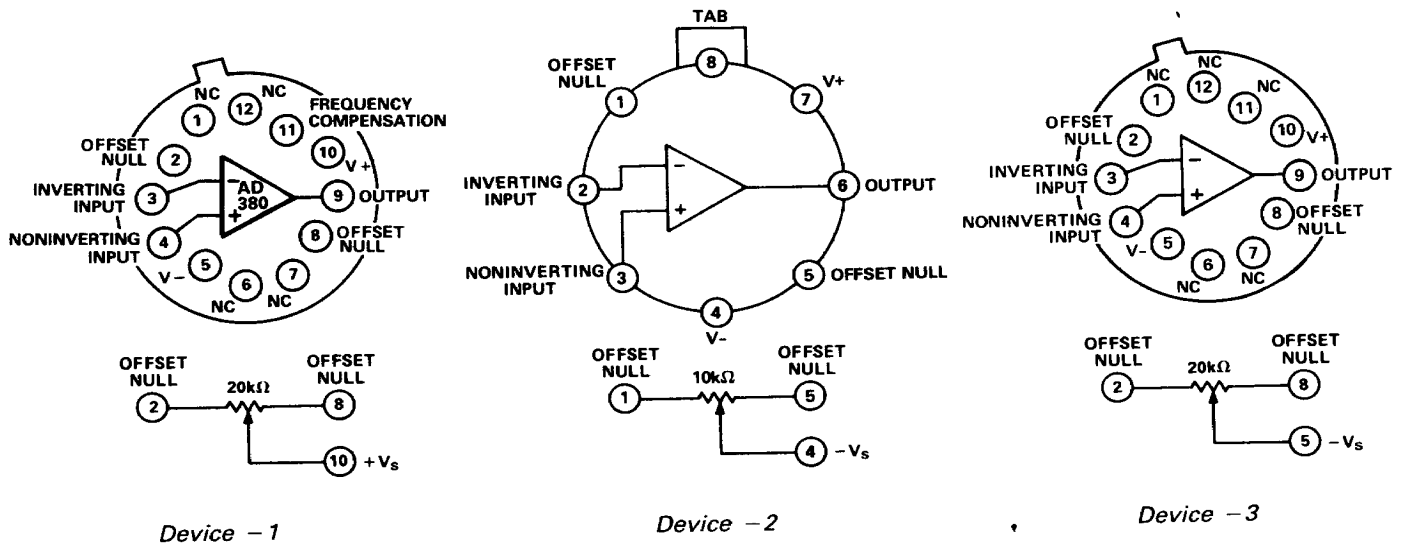
⁴V_{OUT} = +10V to 0V 10kΩ load, V_{OUT} = 0V to –10V 10kΩ load.

Table 1.

REV. C

3.2.1 Functional Block Diagram and Terminal Assignments.

Top View

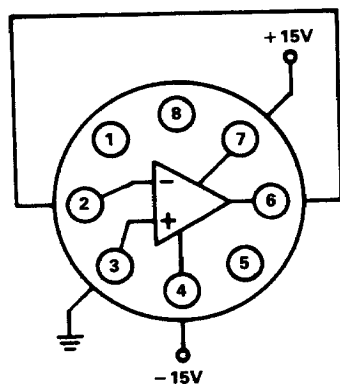


3.2.4 Microcircuit Technology Group.

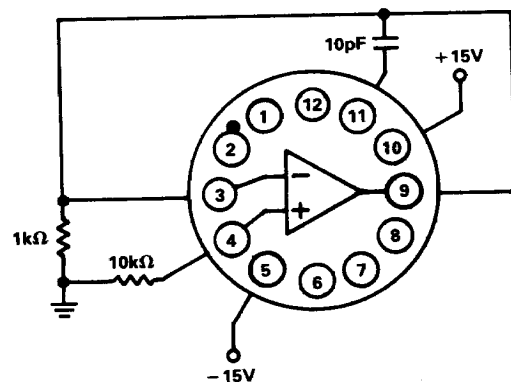
This microcircuit is covered by technology group (I).

4.2.1 Life Test/Burn-In Circuit.

Steady state life test is per MIL-STD-883 Method 1005. Burn-in is per MIL-STD-883 Method 1015 test condition (B).



Device - 2



Device - 1 or -3